

# CSD16342Q5A 25V N-Channel NexFET™ Power MOSFET

#### 1 Features

Optimized for 5V gate drive

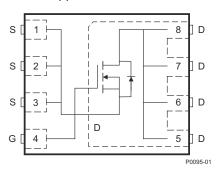
- Resistance rated at  $V_{GS} = 2.5V$
- Ultra low Qg and Qgd
- Low thermal resistance
- Avalanche rated
- Pb free terminal plating
- RoHS compliant
- Halogen free
- SON 5mm x 6mm plastic package

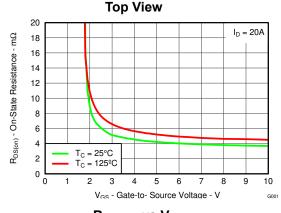
## 2 Applications

- Point-of-load synchronous buck converter for applications in networking, telecom and computing systems
- Optimized for control or synchronous FET applications

## 3 Description

The NexFET™ power MOSFET has been designed to minimize losses in power conversion and optimized for 5V gate drive applications.





R<sub>DS(ON)</sub> vs V<sub>GS</sub>

#### **Product Summary**

V <sub>DS</sub>	Drain to Source Voltage	25	V		
Qg	Gate Charge Total (4.5V)	6.8	6.8		
Q <sub>gd</sub>	Gate Charge Gate to Drain	ge Gate to Drain 1.2		nC	
		V <sub>GS</sub> = 2.5V	6.1	mΩ	
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 4.5V	4.3	mΩ	
		V <sub>GS</sub> = 8V	3.8	mΩ	
V <sub>th</sub>	Threshold Voltage	0.85	V		

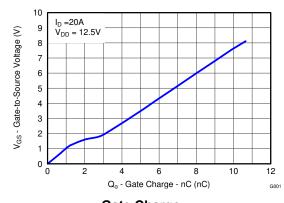
#### **Ordering Information**

Device	Package	Media	Qty	Ship	
CSD16342Q5A	SON 5 × 6 Plastic Package	13-inch reel	2500	Tape and Reel	

**Absolute Maximum Ratings** 

T <sub>A</sub> = 2	5°C unless otherwise stated	VALUE	UNIT
V <sub>DS</sub>	Drain to Source Voltage	25	V
V <sub>GS</sub>	Gate to Source Voltage	+10 / -8	V
	Continuous Drain Current, T <sub>C</sub> = 25°C	100	Α
I <sub>D</sub>	Continuous Drain Current <sup>(1)</sup>	21	Α
I <sub>DM</sub>	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	131	Α
P <sub>D</sub>	Power Dissipation <sup>(1)</sup>	3	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D = 40A$ , $L = 0.1 mH$ , $R_G = 25\Omega$	80	mJ

- Typical  $R_{\theta JA}$  = 40°C/W on 1in<sup>2</sup> Cu (2 oz.) on 0.060" thick FR4 PCB.
- Pulse width ≤300µs, duty cycle ≤2% (2)



**Gate Charge** 



# 4 Specifications

# **4.1 Electrical Characteristics**

(T<sub>A</sub> = 25°C unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static C	haracteristics	,			-	
BV <sub>DSS</sub>	Drain to Source Voltage	V <sub>GS</sub> = 0V, I <sub>DS</sub> = 250μA	25			V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 20V			1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = +10/-8V			100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250 \mu A$	0.6	0.85	1.1	V
		V <sub>GS</sub> = 2.5V, I <sub>DS</sub> = 20A		6.1	7.8	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 4.5V, I <sub>DS</sub> = 20A		4.3	5.5	mΩ
		V <sub>GS</sub> = 8V, I <sub>DS</sub> = 20A		3.8	4.7	mΩ
g <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 15V, I <sub>DS</sub> = 20A		91		S
Dynamic	Characteristics					
C <sub>ISS</sub>	Input Capacitance			1050	1350	pF
Coss	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V, f = 1MHz$		730		pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			53	69	pF
R <sub>g</sub>	Series Gate Resistance			1.5	3	Ω
Qg	Gate Charge Total (4.5V)			6.8	7.1	nC
Q <sub>gd</sub>	Gate Charge Gate to Drain	V <sub>DS</sub> = 12.5V, I <sub>D</sub> = 20A		0.9		nC
Q <sub>gs</sub>	Gate Charge Gate to Source	V <sub>DS</sub> - 12.5V, I <sub>D</sub> - 20A		1.9		nC
Qg(th)	Gate Charge at Vth			1.2		nC
Q <sub>OSS</sub>	Output Charge	V <sub>DS</sub> = 13V, V <sub>GS</sub> = 0V		13.7		nC
t <sub>d(on)</sub>	Turn On Delay Time			5.2		ns
t <sub>r</sub>	Rise Time	V <sub>DS</sub> = 12.5V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A ,		16.6		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$R_G = 2\Omega$		13.4		ns
t <sub>f</sub>	Fall Time			3.1		ns
Diode C	haracteristics				'	
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> = 20A, V <sub>GS</sub> = 0V		0.8	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	V <sub>DD</sub> = 13V, I <sub>E</sub> = 20A, di/dt = 300A/µs		14.5		nC
t <sub>rr</sub>	Reverse Recovery Time	V <sub>DD</sub> - 13V, 1 <sub>F</sub> - 2UA, αι/αι - 30UA/μS		20		ns

Product Folder Links: CSD16342Q5A

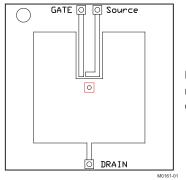


#### 4.2 Thermal Characteristics

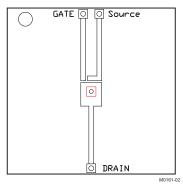
(T<sub>A</sub> = 25°C unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case <sup>(1)</sup>			1.2	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient <sup>(1)</sup> (2)			50	°C/W

- R<sub>θJC</sub> is determined with the device mounted on a 1-inch² (6.45cm²), 2oz. (0.071mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81cm × 3.81cm), 0.06-inch (1.52mm) thick FR4 PCB. R<sub>θJC</sub> is specified by design, whereas R<sub>θJA</sub> is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45cm<sup>2</sup>), 2oz. (0.071mm thick) Cu.



Max  $R_{\theta JA}$  = 50°C/W when mounted on 1 inch<sup>2</sup> of 2oz. Cu.



Max  $R_{\theta JA}$  = 123°C/W when mounted on minimum pad area of 2oz. Cu.

# **5 Typical MOSFET Characteristics**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

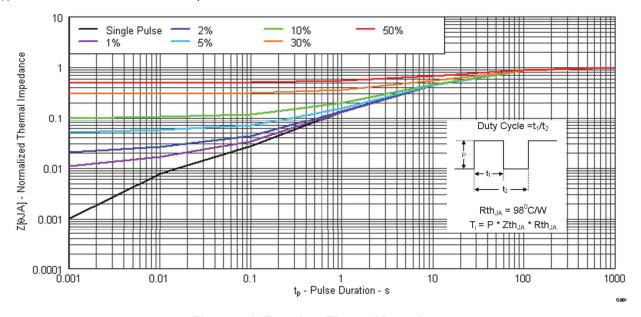
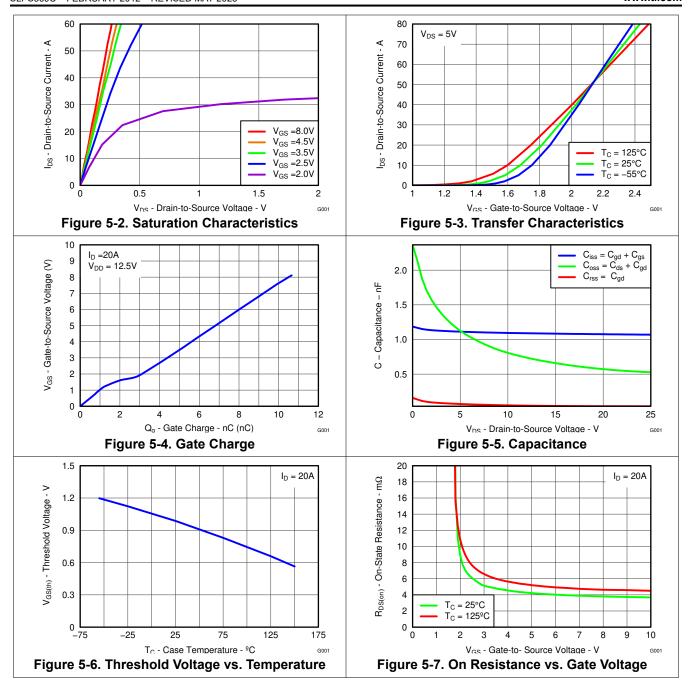
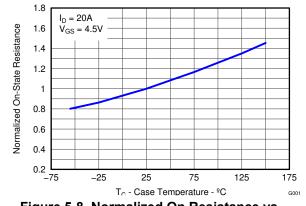


Figure 5-1. Transient Thermal Impedance







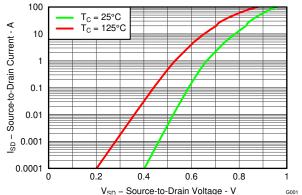
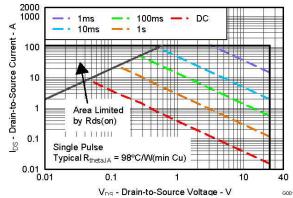


Figure 5-8. Normalized On Resistance vs.
Temperature

Figure 5-9. Typical Diode Forward Voltage



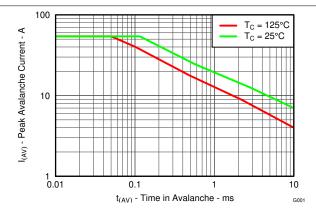


Figure 5-10. Maximum Safe Operating Area

Figure 5-11. Single Pulse Unclamped Inductive Switching

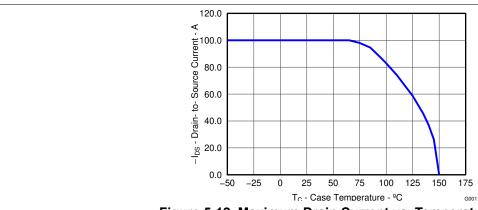


Figure 5-12. Maximum Drain Current vs. Temperature



# **6 Revision History**

N	OTE: Page numbers for previous revisions may differ from page numbers in the current version.	
C	hanges from Revision B (January 2025) to Revision C (May 2025)	Page
•	Updated the document title from CSD16342Q5A 40V N-Channel NexFET <sup>TM</sup> Power MOSFET to CSD16342Q5A 25V N-Channel NexFET <sup>TM</sup> Power MOSFET	1
_	hanges from Revision A (March 2012) to Revision B (January 2025)	Page
_	Changes from Revision A (March 2012) to Revision B (January 2025)  Updated the numbering format for tables, figures, and cross-references throughout the document	
-	, , , , ,	



# 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	<b>RoHS</b> (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
CSD16342Q5A	Active	Production	VSONP (DQJ)   8	2500   LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD16342
CSD16342Q5A.B	Active	Production	VSONP (DQJ)   8	2500   LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD16342

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 13-May-2025

#### TAPE AND REEL INFORMATION



# TAPE DIMENSIONS KO P1 BO W Cavity A0

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	U	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16342Q5A	VSONP	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

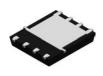
# **PACKAGE MATERIALS INFORMATION**

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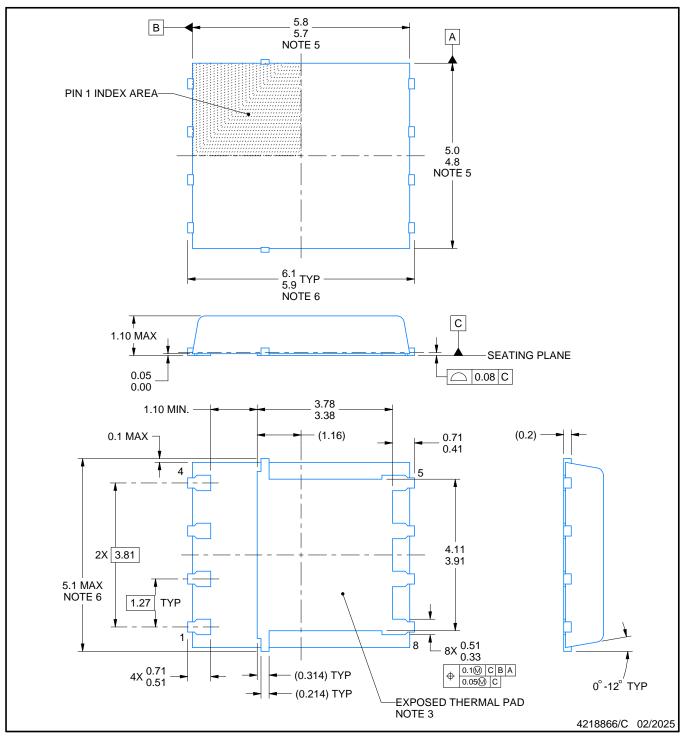


#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CSD16342Q5A	VSONP	DQJ	8	2500	340.0	340.0	38.0	



PLASTIC SMALL OUTLINE - NO LEAD

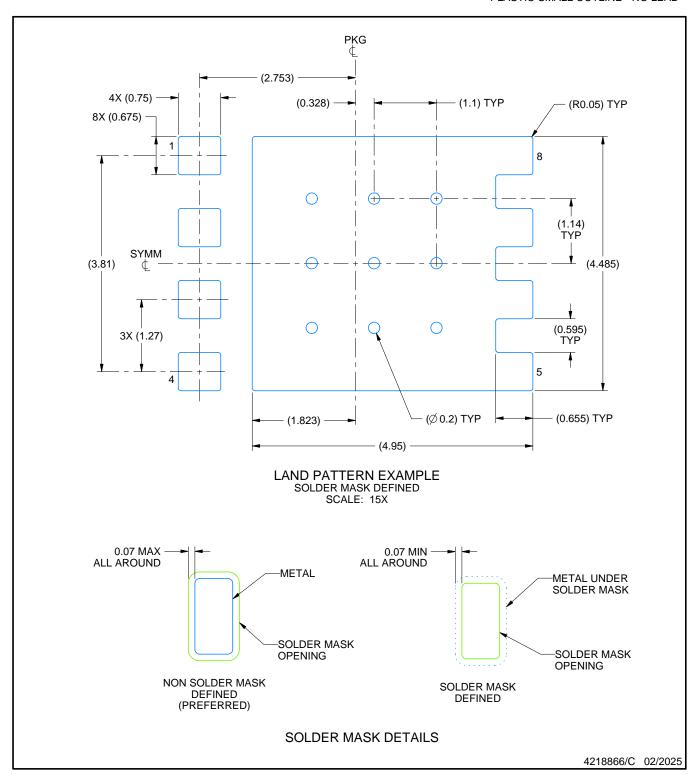


#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.
- Metalized features are supplier options and may not be on the package.
   These dimensions do not include mold flash protrusions or gate burrs.
- 6. These dimensions include interterminal flash or protrusion. Interterminal flash or protrusion shall not exceed 0.25 mm per side.



PLASTIC SMALL OUTLINE - NO LEAD

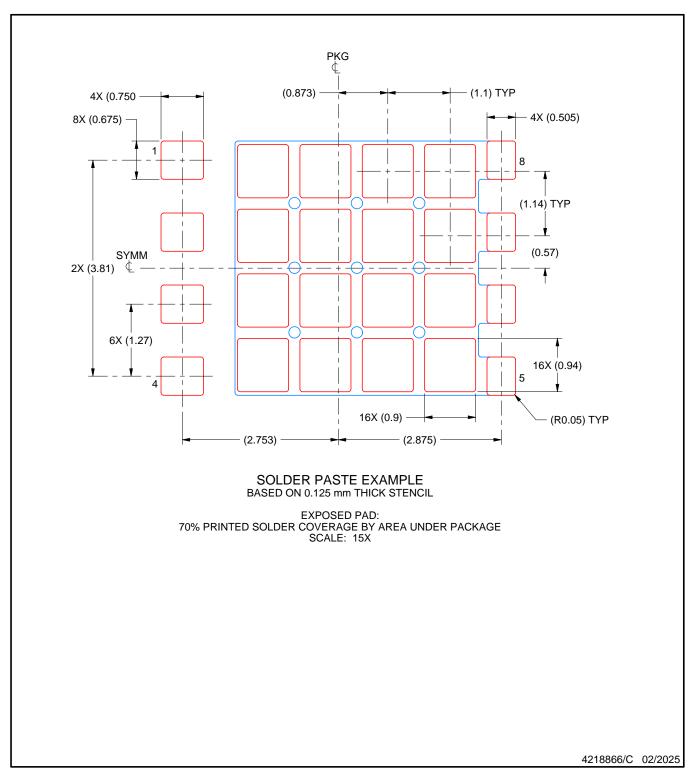


NOTES: (continued)

- 7. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 8. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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